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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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# **N-Channel Power MOSFET**

700V, 8A, 0.6Ω

#### **FEATURES**

- Super-Junction technology
- High performance, small R<sub>DS(ON)</sub>\*Q<sub>g</sub> figure of merit (FOM)
- High ruggedness performance
- 100% UIS and R<sub>g</sub> tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER VALUE UNIT				
$V_{DS}$	700	V		
R <sub>DS(on)</sub> (max)	0.6	Ω		
$Q_g$	12.6	nC		

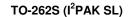




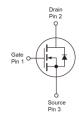


## **APPLICATIONS**

- Power Supply
- AC/DC LED Lighting







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	700	V
Gate-Source Voltage		V <sub>GS</sub>	±30	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		8	А
	$T_C = 100$ °C	I <sub>D</sub>	4.6	Α
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	24	Α
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>D</sub>	83	W
Single Pulse Avalanche Energy (Note 3)		E <sub>AS</sub>	100	mJ
Single Pulse Avalanche Current (Note	3)	I <sub>AS</sub>	2	Α
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	1.5	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

**Thermal Performance Note:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

1



ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	МАХ	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.0	2.9	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Drain-Source On-State Resistance (Note 4)	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.4A	R <sub>DS(on)</sub>		0.53	0.6	Ω
Dynamic (Note 5)		•			l	
Total Gate Charge	$V_{DS} = 380V, I_{D} = 8A,$ $V_{GS} = 10V$	Qg		12.6		
Gate-Source Charge		$Q_{gs}$		2.9		nC
Gate-Drain Charge		$Q_{gd}$		4.5		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		743		
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		63		pF
Gate Resistance	f = 1.0MHz	$R_g$		3.6	7.2	Ω
Switching (Note 6)	Switching (Note 6)					
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 8A, V_{GS} = 10V$	t <sub>d(on)</sub>		36		
Turn-On Rise Time		t <sub>r</sub>		21		
Turn-Off Delay Time		t <sub>d(off)</sub>		95		ns
Turn-Off Fall Time		t <sub>f</sub>		21		-
Source-Drain Diode						
Forward On Voltage (Note 4)	I <sub>S</sub> = 8A, V <sub>GS</sub> = 0V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	$V_R=200V, I_S=4A$ $dI_F/dt=100A/\mu s$	t <sub>rr</sub>		187.9		ns
Reverse Recovery Charge		$Q_{rr}$	-	1.4		μC

#### Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 50mH,  $I_{AS} = 2A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 4. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

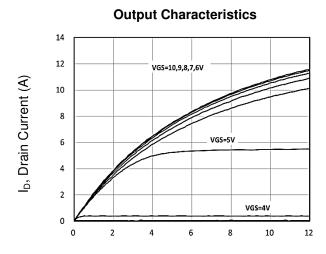
# **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM70N600ACL X0G	TO-262S (I <sup>2</sup> PAK SL)	50pcs / Tube

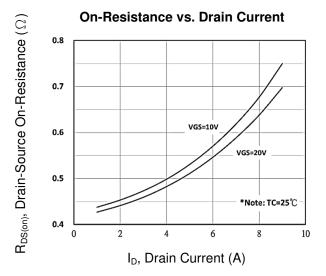


## **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 



 $V_{\text{DS}}$ , Drain to Source Voltage (V)



On-Resistance vs. Junction Temperature

3.0

Unumalized On-Resistance vs. Junction Temperature

3.0

2.5

Notes:
1. VGS=10V
2. ID=4A

0.0

40

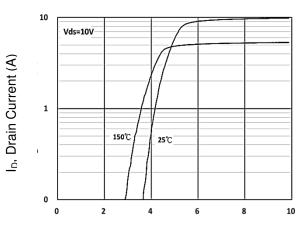
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120

160

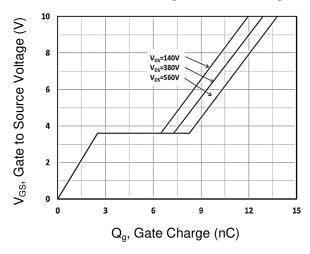
T<sub>J</sub>, Junction Temperature (°C)

**Transfer Characteristics** 

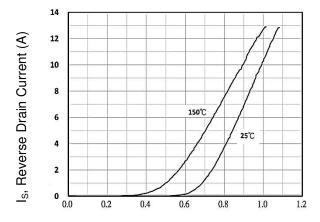


V<sub>GS</sub>, Gate to Source Voltage (V)

# Gate-Source Voltage vs. Gate Charge



Source-Drain Diode Forward Current vs. Voltage



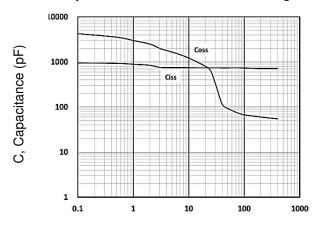
V<sub>SD</sub>, Body Diode Forward Voltage (V)



#### **CHARACTERISTICS CURVES**

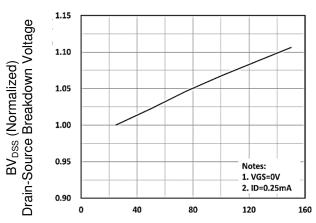
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

# Capacitance vs. Drain-Source Voltage



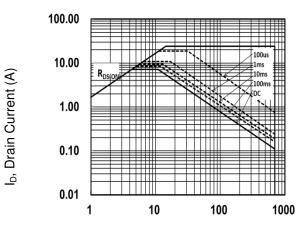
V<sub>DS</sub>, Drain to Source Voltage (V)

# BV<sub>DSS</sub> vs. Junction Temperature



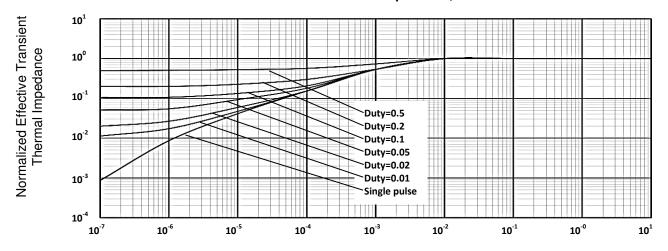
T<sub>J</sub>, Junction Temperature (°C)

# Maximum Safe Operating Area, Junction-to-Case



 $V_{\text{DS}}$ , Drain to Source Voltage (V)

#### Normalized Thermal Transient Impedance, Junction-to-Case



t, Square Wave Pulse Duration (sec)

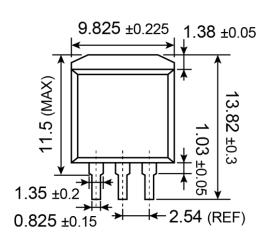
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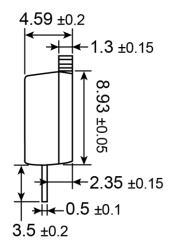


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# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

## TO-262S





# **MARKING DIAGRAM**



**G** = Halogen Free

Y = Year Code

WW = Week Code (01~52)

**F** = Factory Code

Version: A1609

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